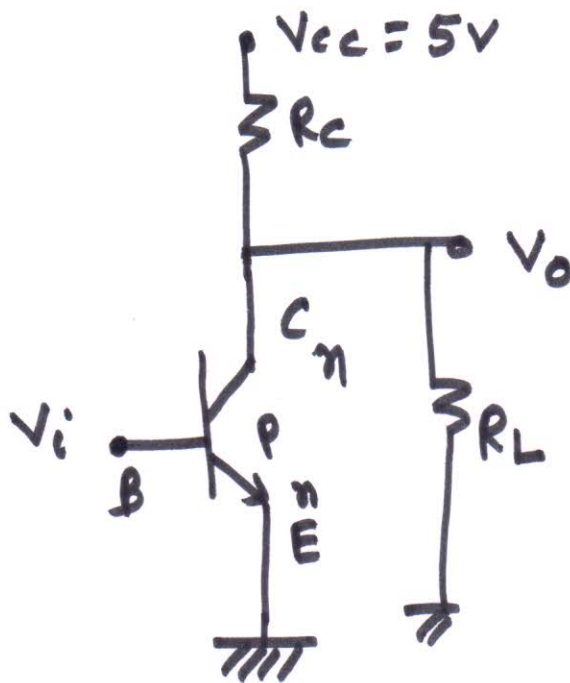


Applications

Amplification	Switching
<ul style="list-style-type: none"> Active <div style="margin-left: 20px;"> $\left. \begin{array}{l} \text{BE Jun.} \rightarrow \text{F.B} \\ \text{BC Jun.} \rightarrow \text{R.B} \end{array} \right\}$ $I_C = \beta I_B$ $V_{BE} = 0.7 \text{ V}$ $V_{CE} > 0.2 \text{ V}$ </div> 	<ul style="list-style-type: none"> Cut off <div style="margin-left: 20px;"> $\begin{array}{l} \text{BE Jun.} \rightarrow \text{R.B} \\ \text{BC Jun.} \rightarrow \text{R.B} \end{array}$ $I_B = I_C = I_E = 0$ <p>(open ckt)</p> <p>'OFF'</p> </div> Saturation <div style="margin-left: 20px;"> $\begin{array}{l} \text{BE Jun.} \rightarrow \text{F.B} \\ \text{BC Jun.} \rightarrow \text{F.B} \end{array}$ $V_{CE_{\text{sat}}} = 0.2 \text{ V} \approx 0 \text{ V}$ <p>(Short ckt)</p> <p>'ON'</p> $I_C < \beta I_B$ </div>

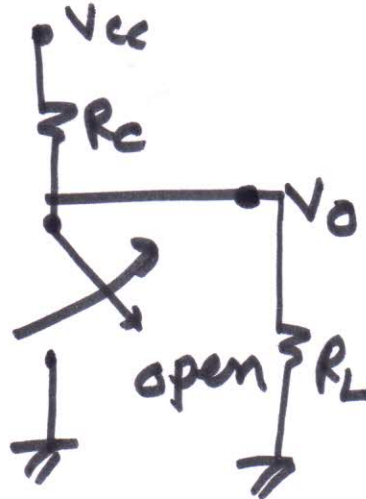
N07



Case 1:

$V_i = 0V$

Transistor \rightarrow 'cut off'



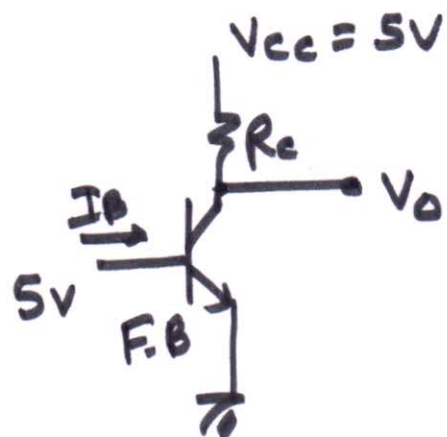
$$V_o = \frac{R_L}{R_c + R_L} \times V_{cc}$$

$V_o \rightarrow$ 'high'

$$\Rightarrow V_i \rightarrow '0' \Rightarrow V_o \rightarrow '1'$$

Case 2:

$$V_i = 5V$$

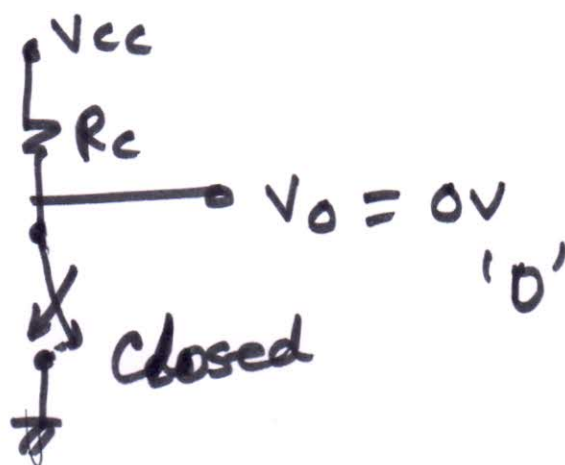


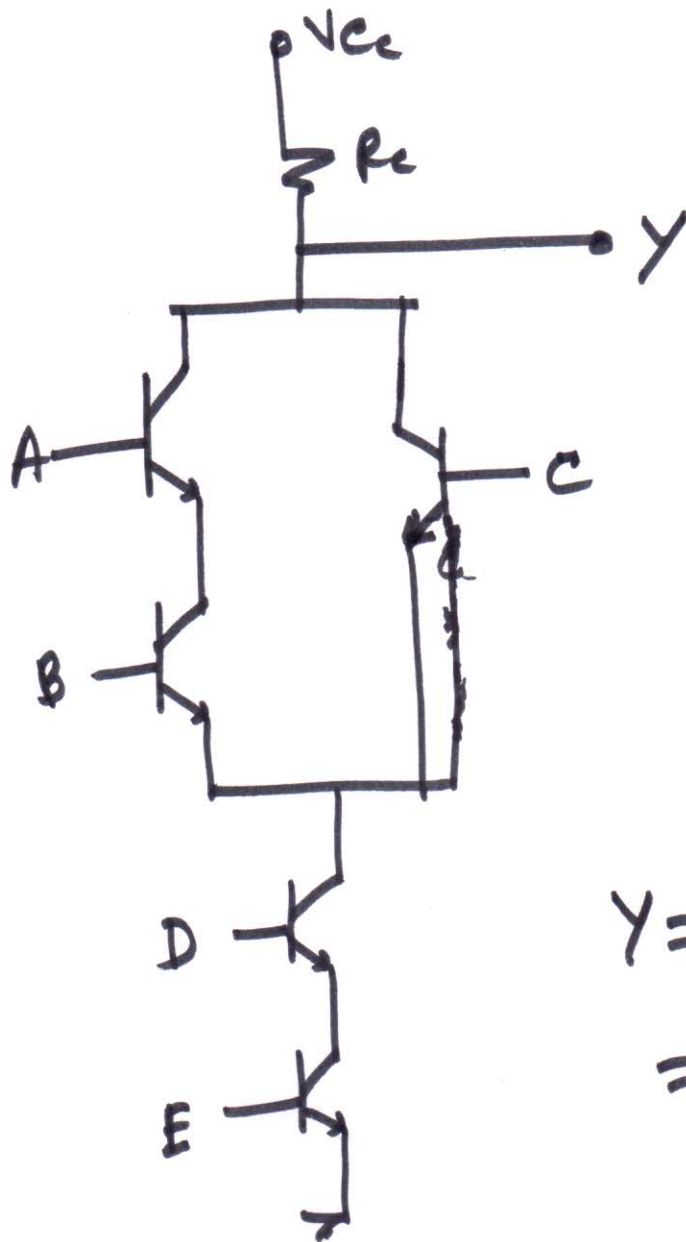
Saturation Region

$$V_{CE} = 0.2V$$

$$\approx 0V$$

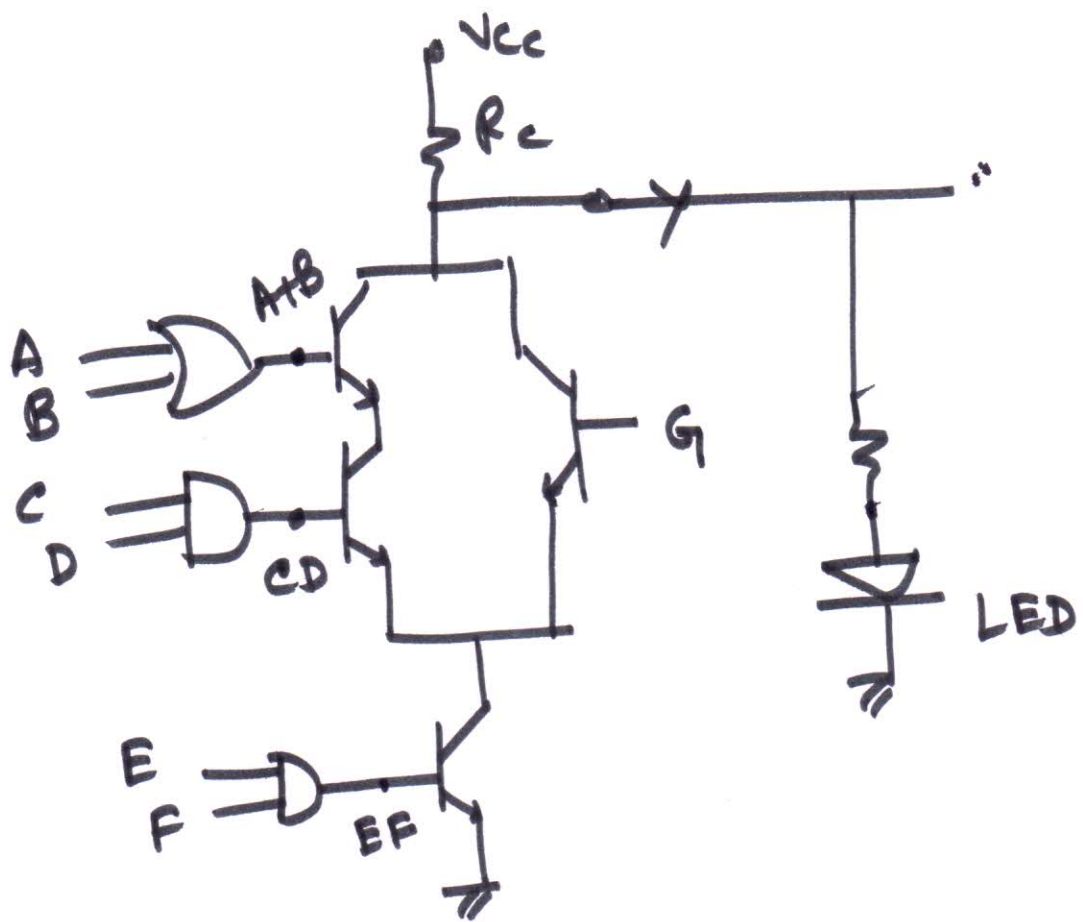
(Short ckt)





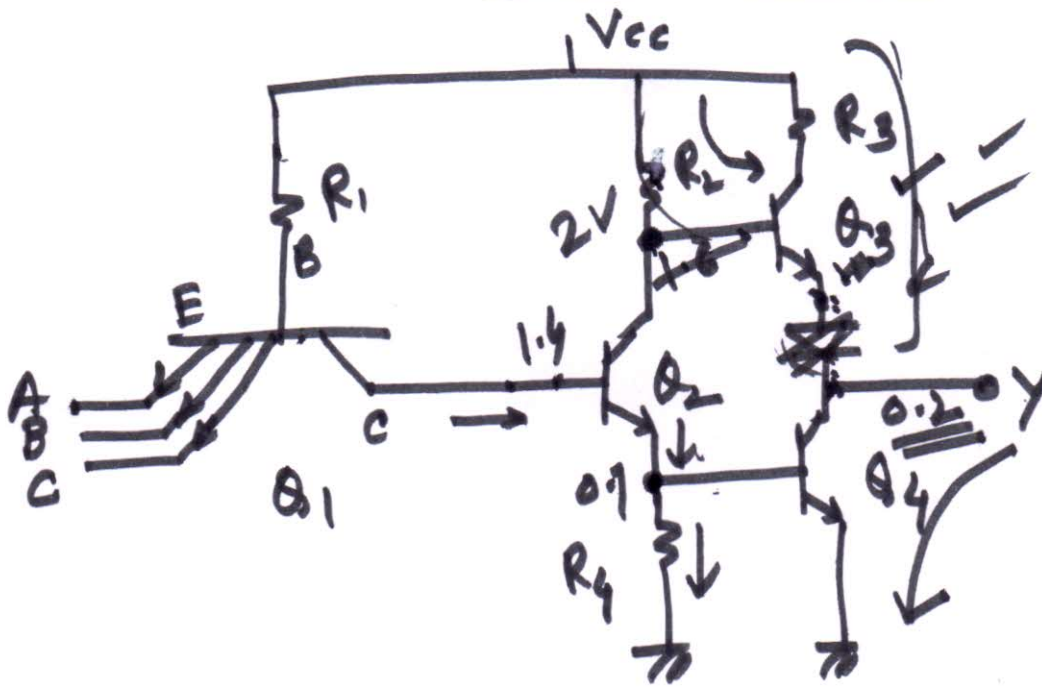
$$Y = \overline{ABDE + CDE}$$

$$= \overline{(AB + C)DE}$$



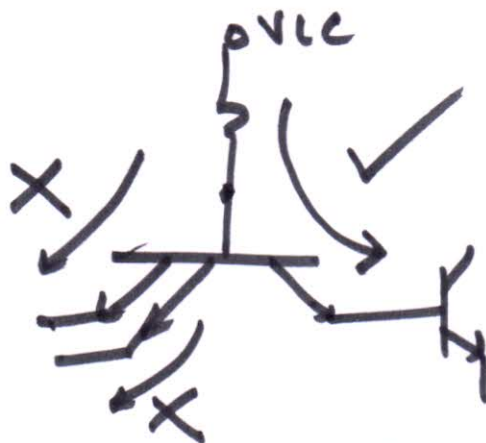
$$Y = \overline{[(A+B)CD + G]EF}$$

TTL NAND



Case 1:

When all the V_p s are high ('1').



BE Junction \rightarrow R.B

BC Jun. \rightarrow F.B

$Q_1 \rightarrow$ Inverse Active

$Q_2 \rightarrow$ 'ON' / saturation

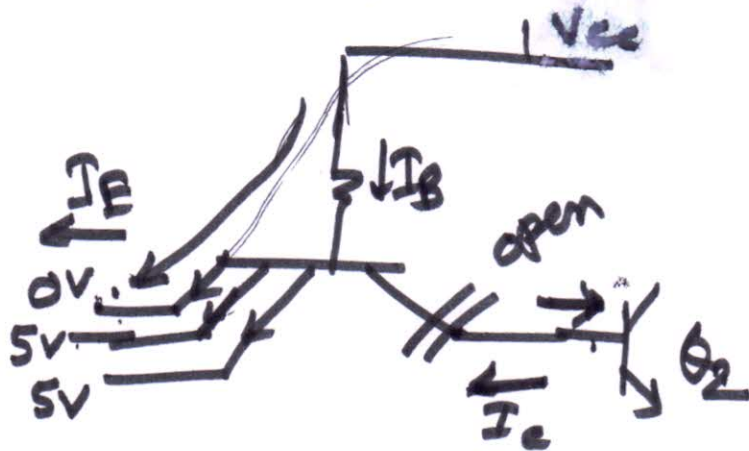
$Q_4 \rightarrow$ 'Sat'

$Q_3 \rightarrow$ 'ON' / 'OFF' \rightarrow preferable
(if diode is used)
& Q_2 is in saturation

$Y = '0'$

Case 2:

If any ^{one} i/p is low



$Q_2 \rightarrow \text{'OFF'}$

$Q_1 \rightarrow \text{'OFF'}$

$Y = '1'$